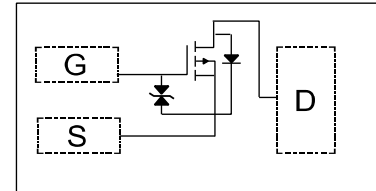


## Description

The MOSFET provide the best combination of fast switching, low on-resistance and cost-effectiveness.

**MOSFET Product Summary**

| $V_{DS}(V)$ | $R_{DS(on)}(\Omega)$ | $I_D(mA)$ |
|-------------|----------------------|-----------|
| -20         | 0.45@ $V_{GS}=-4.5V$ | -800      |
|             | 0.62@ $V_{GS}=-2.5V$ |           |
|             | 0.86@ $V_{GS}=-1.8V$ |           |



**Top View**

## Absolute maximum rating@25°C

| Parameter                                     |                  | Symbol    | Value       | Units      |
|-----------------------------------------------|------------------|-----------|-------------|------------|
| Drain-Source Voltage                          |                  | $V_{DS}$  | -20         | V          |
| Gate-Source Voltage                           |                  | $V_{GS}$  | $\pm 10$    | V          |
| Continuous Drain Current                      | Continuous       | $I_D$     | -800        | mA         |
|                                               | Pulsed           | $I_{DP}$  | -1200       |            |
| Maximum Power Dissipation<br>(Note 1)(Note 4) | $T_A=25^\circ C$ | $P_D$     | 270         | mW         |
|                                               | $T_A=70^\circ C$ |           | 170         |            |
| Maximum Power Dissipation<br>(Note 2)(Note 4) | $T_A=25^\circ C$ | $P_D$     | 240         | mW         |
|                                               | $T_A=70^\circ C$ |           | 150         |            |
| Pulsed Drain Current(Note 3)                  |                  | $I_{DM}$  | -1.2        | A          |
| Operating Junction Temperature                |                  | $T_J$     | 150         | $^\circ C$ |
| Lead Temperature                              |                  | $T_L$     | 260         | $^\circ C$ |
| Storage Temperature Range                     |                  | $T_{stg}$ | -55 to +150 | $^\circ C$ |

## Thermal resistance

| Parameter                                          |                      | Symbol          | Min. | Typ. | Max. | Units        |
|----------------------------------------------------|----------------------|-----------------|------|------|------|--------------|
| Junction-to-Ambient Thermal Resistance<br>(Note 1) | $t \leq 10\text{ s}$ | $R_{\theta JA}$ | -    | 350  | 400  | $^\circ C/W$ |
|                                                    | Steady State         |                 | -    | 395  | 460  | $^\circ C/W$ |
| Junction-to-Ambient Thermal Resistance (Note 2)    | $t \leq 10\text{ s}$ | $R_{\theta JA}$ | -    | 390  | 445  | $^\circ C/W$ |
|                                                    | Steady State         |                 | -    | 450  | 515  | $^\circ C/W$ |
| Junction-to-Case Thermal Resistance                | Steady State         | $R_{\theta JA}$ | -    | 245  | 290  | $^\circ C/W$ |

## Electrical characteristics per line@25°C ( unless otherwise specified)

| Parameter                                 | Symbol              | Conditions                                                                                      | Min.  | Typ.  | Max.  | Units |
|-------------------------------------------|---------------------|-------------------------------------------------------------------------------------------------|-------|-------|-------|-------|
| OFF CHARACTERISTICS                       |                     |                                                                                                 |       |       |       |       |
| Drain-to-Source Breakdown Voltage         | BV <sub>DSS</sub>   | I <sub>D</sub> =-250uA, V <sub>GS</sub> =0V                                                     | -20   | -     | -     | V     |
| Zero Gate Voltage Drain Current           | I <sub>DSS</sub>    | V <sub>DS</sub> =-16V, V <sub>GS</sub> =0V                                                      | -     | -     | -1    | μA    |
| Gate-to-source Leakage Current            | I <sub>GSS</sub>    | V <sub>DS</sub> =0V, V <sub>GS</sub> =±8V                                                       | -     | -     | ±10   | μA    |
| ON CHARACTERISTICS                        |                     |                                                                                                 |       |       |       |       |
| Gate Threshold Voltage                    | V <sub>GS(th)</sub> | V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = -250uA                                     | -0.45 | -0.55 | -0.85 | V     |
| Drain-to-source On-resistance (Note 5)    | R <sub>DS(ON)</sub> | V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-700mA                                                  | -     | 450   | 700   | mΩ    |
|                                           |                     | V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-300mA                                                  | -     | 620   | 850   | mΩ    |
|                                           |                     | V <sub>GS</sub> =-1.8V, I <sub>D</sub> =-100mA                                                  | -     | 1000  | 1500  | mΩ    |
| Forward Transconductance                  | g <sub>FS</sub>     | V <sub>DS</sub> =-5V, I <sub>D</sub> =-450mA                                                    | -     | 1.25  | -     | s     |
| CHARGES, CAPACITANCES AND GATE RESISTANCE |                     |                                                                                                 |       |       |       |       |
| Input Capacitance                         | C <sub>ISS</sub>    | V <sub>GS</sub> =0V, V <sub>DS</sub> =-10V,<br>f=1MHz                                           | -     | 72    | -     | pF    |
| Output Capacitance                        | C <sub>OSS</sub>    |                                                                                                 | -     | 9.5   | -     | pF    |
| Reverse Transfer Capacitance              | C <sub>RSS</sub>    |                                                                                                 | -     | 9.8   | -     | pF    |
| Total Gate Charge                         | Q <sub>G(TOT)</sub> | V <sub>GS</sub> =-4.5V, V <sub>DS</sub> =-10V,<br>I <sub>D</sub> =-450mA                        | -     | 0.9   | -     | nC    |
| Threshold Gate Charge                     | Q <sub>G(TH)</sub>  |                                                                                                 | -     | 0.1   | -     | nC    |
| Gate-to-Source Charge                     | Q <sub>GS</sub>     |                                                                                                 | -     | 0.15  | -     | nC    |
| Gate-to-Drain Charge                      | Q <sub>GD</sub>     |                                                                                                 | -     | 0.3   | -     | nC    |
| SWITCHING CHARACTERISTICS                 |                     |                                                                                                 |       |       |       |       |
| Turn-On Delay Time                        | td(ON)              | V <sub>GS</sub> =-4.5V, V <sub>DS</sub> =-10V ,<br>I <sub>D</sub> =-450mA<br>R <sub>G</sub> =6Ω | -     | 43    | -     | nS    |
| Rise Time                                 | tr                  |                                                                                                 | -     | 137   | -     | nS    |
| Turn-Off Delay Time                       | td(OFF)             |                                                                                                 | -     | 1450  | -     | nS    |
| Fall Time                                 | tf                  |                                                                                                 | -     | 2050  | -     | nS    |
| BODY DIODE CHARACTERISTICS                |                     |                                                                                                 |       |       |       |       |
| Forward Voltage                           | V <sub>SD</sub>     | V <sub>GS</sub> =0V, I <sub>S</sub> =-150mA                                                     | -0.5  | -0.65 | -1.1  | V     |

Note:

1. Surface mounted on FR4 Board using 1 square inch pad size, 1oz copper
2. Surface mounted on FR4 board using minimum pad size, 1oz copper
3. Pulse width < 380 $\mu$ s, Single pulse
4. Maximum junction temperature  $T_J = 150^\circ C$ .
5. Pulse test: Pulse width < 380 us duty cycle < 2%.

## Typical Characteristics

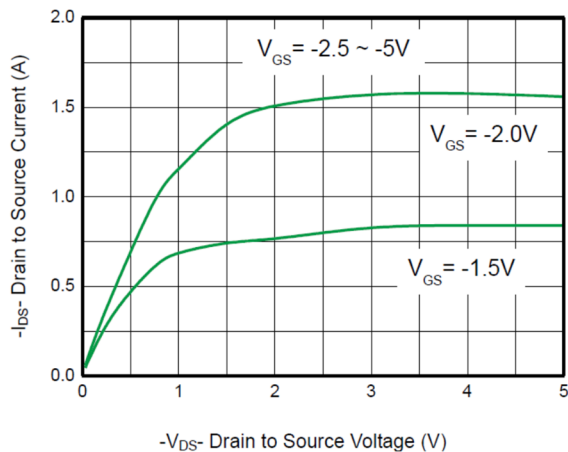


Fig 1. Output characteristics

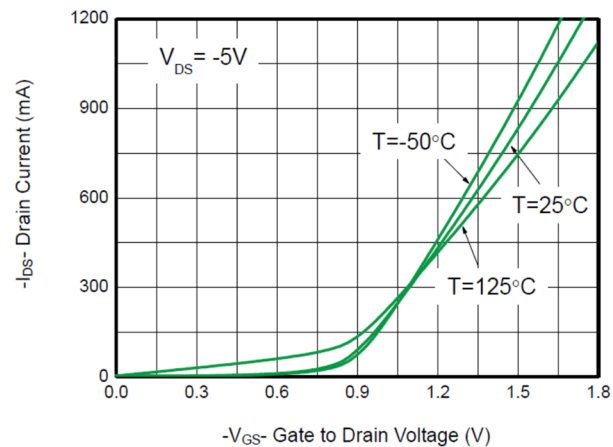


Fig 2. Transfer characteristics

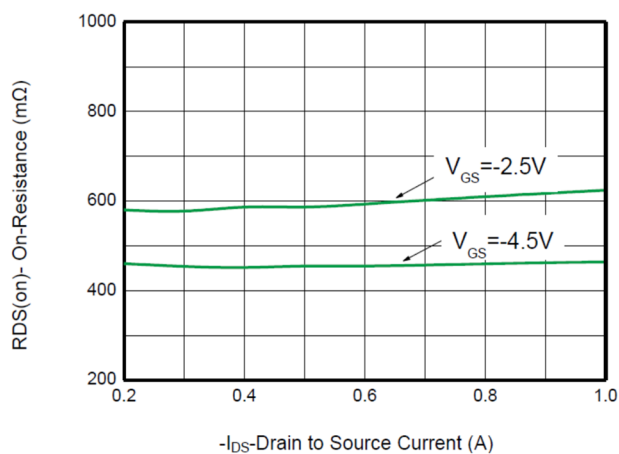


Fig 3. On-Resistance vs. Drain current

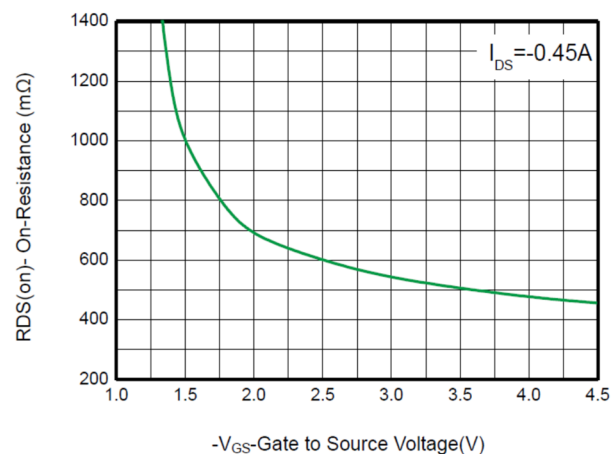


Fig 4. On-Resistance vs. Gate-to-Source voltage

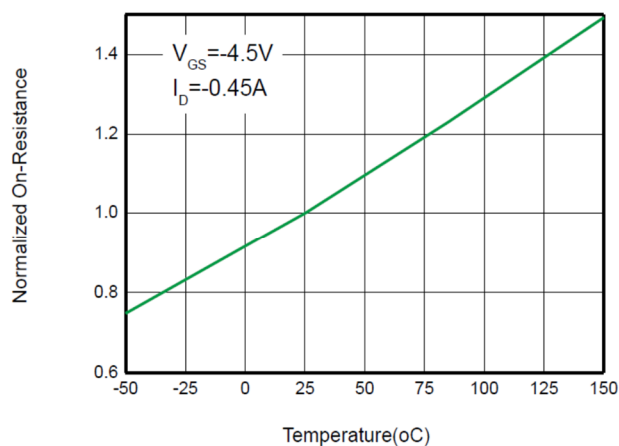


Fig 5. On-Resistance vs. Junction temperature

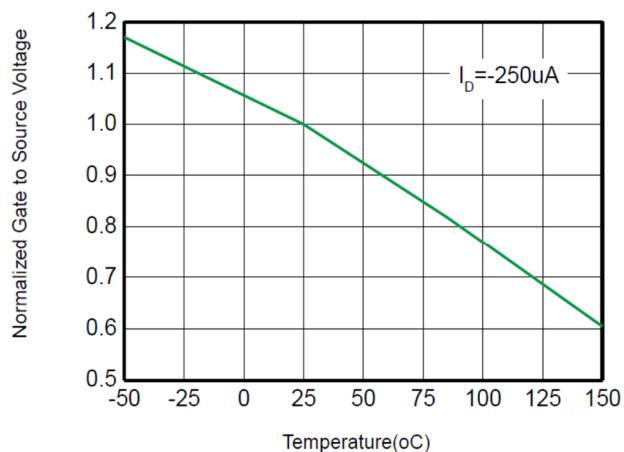


Fig 6. Threshold voltage vs. Temperature

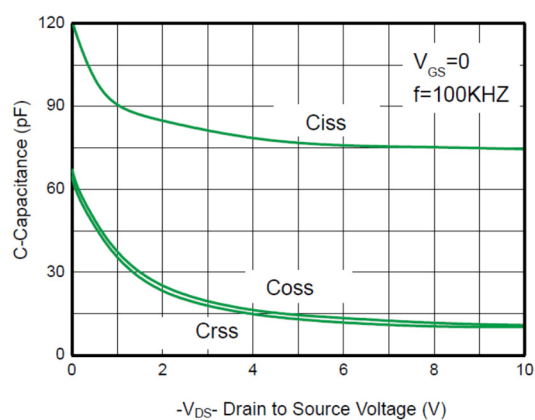


Fig 7. Capacitance.

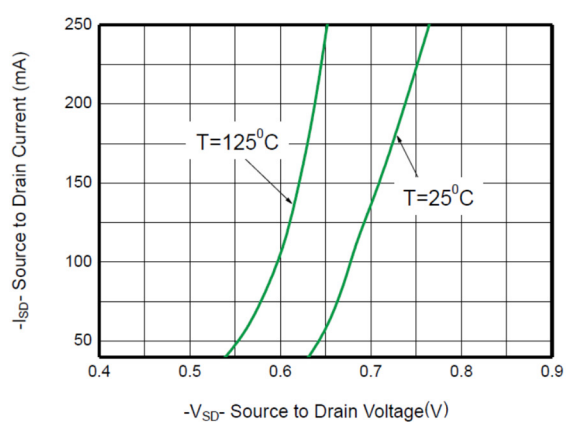
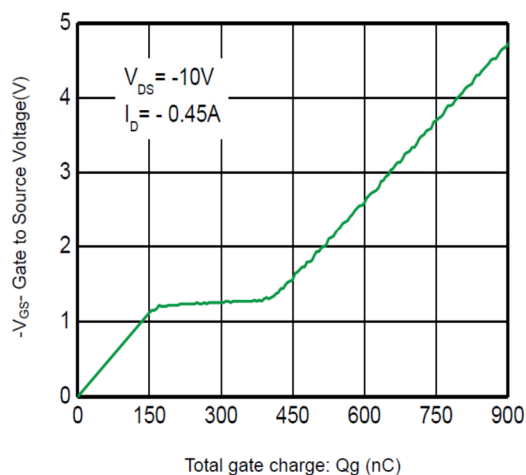
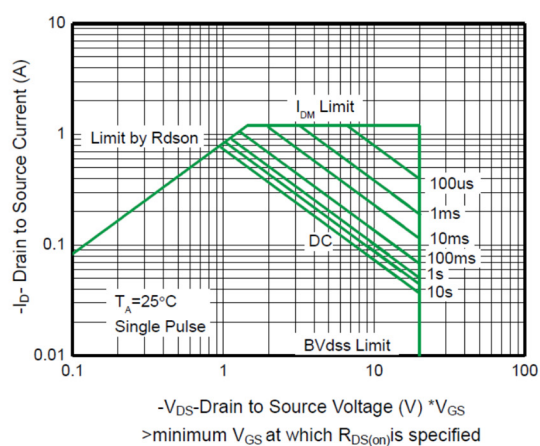
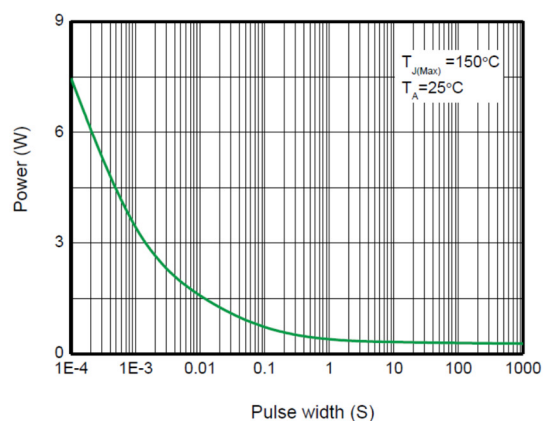
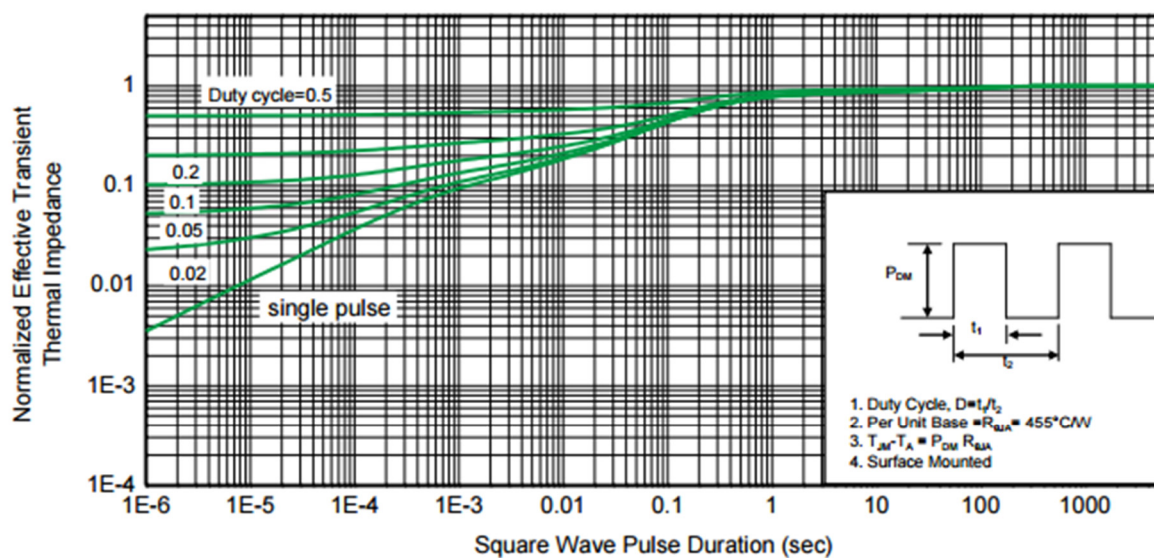


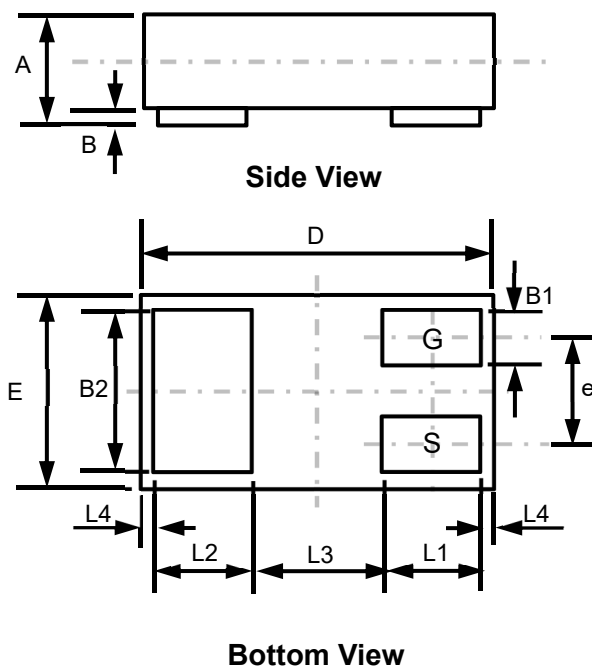
Fig 8. Body diode forward voltage



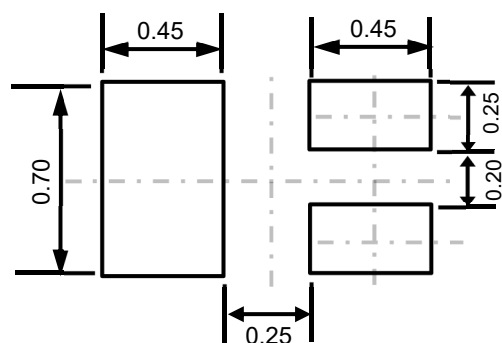


**Transient thermal response (Junction-to-Ambient)**

## Product dimension (DFN1006-3L)



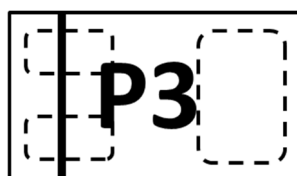
| Dim | Millimeters |      |       |
|-----|-------------|------|-------|
|     | MIN         | Typ  | MAX   |
| A   | 0.33        | 0.47 | 0.498 |
| B   | 0.00        | 0.03 | 0.05  |
| B1  | 0.10        | 0.15 | 0.20  |
| B2  | 0.45        | 0.50 | 0.55  |
| D   | 0.85        | 1.00 | 1.15  |
| E   | 0.45        | 0.60 | 0.75  |
| e   | --          | 0.35 | --    |
| L1  | 0.20        | 0.25 | 0.30  |
| L2  | 0.20        | 0.25 | 0.30  |
| L3  | --          | 0.39 | --    |
| L4  | --          | 0.05 | --    |



Suggested PCB Layout

Unit:mm

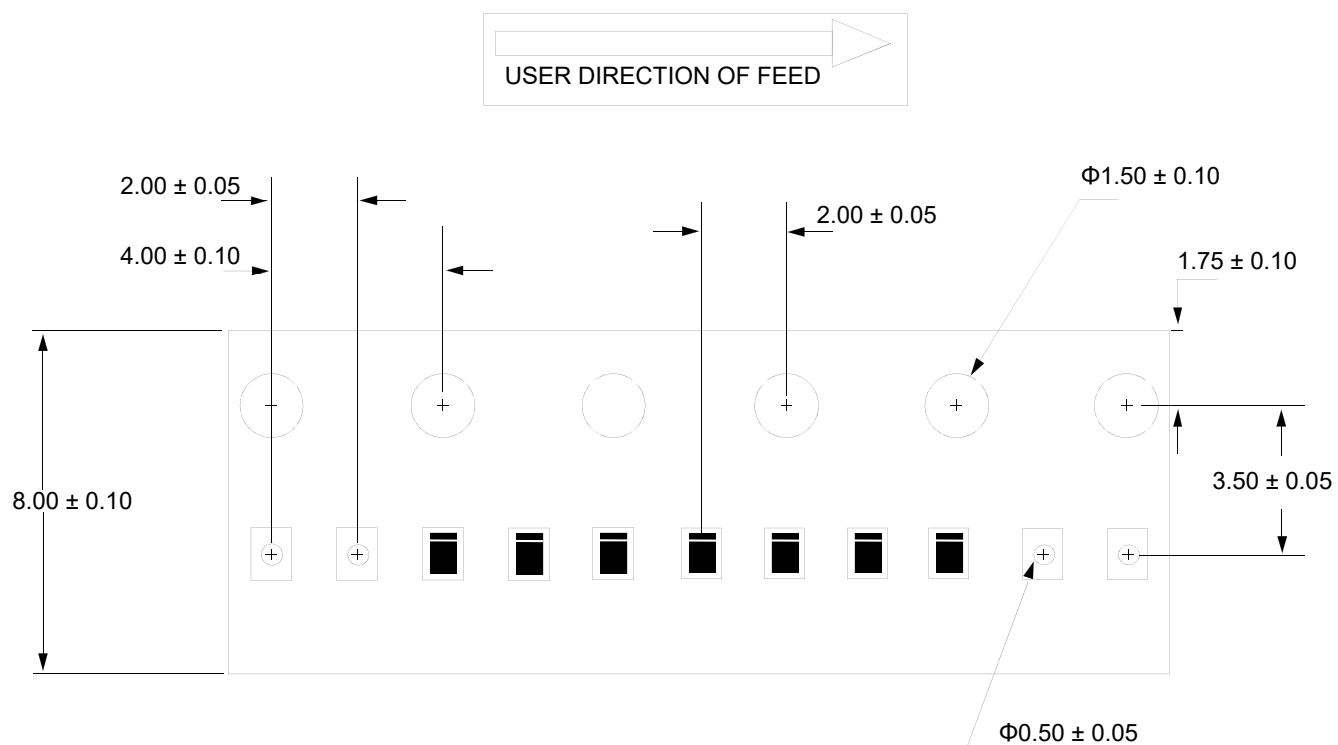
## Marking information



## Ordering information

| Device      | Package             | Reel | Shipping            |
|-------------|---------------------|------|---------------------|
| PPM3FD20V1E | DFN1006-3L(Pb-Free) | 7"   | 10000 / Tape & Reel |

## Load with information



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